

ABSTRACT OF THE DISCLOSURE

POROUS LOW DIELECTRIC CONSTANT COMPOSITIONS AND METHODS FOR MAKING AND USING SAME

5 A porous organosilicate glass (OSG) film: $\text{Si}_v\text{O}_w\text{C}_x\text{H}_y\text{F}_z$, where $v+w+x+y+z = 100\%$, v is 10 to 35 atomic%, w is 10 to 65 atomic%, x is 5 to 30 atomic%, y is 10 to 50 atomic% and z is 0 to 15 atomic%, has a silicate network with carbon bonds as methyl groups (Si-CH_3) and contains pores with diameter less than 3nm equivalent spherical diameter and dielectric constant less than 2.7. A preliminary film is deposited by a chemical vapor deposition method from organosilane and/or organosiloxane precursors, and independent pore-forming precursors. Porogen precursors form pores within the preliminary film and are subsequently removed to provide the porous film.

10 Compositions, film forming kits, include organosilane and/or organosiloxane compounds containing at least one Si-H bond and porogen precursors of hydrocarbons containing alcohol, ether, carbonyl, carboxylic acid, ester, nitro, primary amine, secondary amine, and/or tertiary amine functionality or combinations.

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